L Number	Hits	Search Text	DB	Time stamp
1	65	STI and buried and (interlayer with	USPAT;	2004/02/21
1 -		dielectric) and plug and (doping or	US-PGPUB	10:03
		implantation or implanting) and memory		
2	65		USPAT;	2004/02/21
-		dielectric) and plug and (doping or	US-PGPUB	10:11
		implantation or implanting) and memory)		
		and @ad<20030820		
3	0	STI and buried and (interlayer with	EPO; JPO;	2004/02/21
		dielectric) and plug and (doping or	DERWENT;	10:00
		implantation or implanting) and memory	IBM_TDB	
4	5	((STI and buried and (interlayer with	USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:03
		implantation or implanting) and memory)		
		and @ad<20030820) and diode		
5	5	STI and buried and (interlayer with	USPAT;	2004/02/21
		dielectric) and plug and (doping or	US-PGPUB	10:04
		implantation or implanting) and memory		
		and diode		0004/00/01
6	5	(isolation with trench) and buried and	USPAT;	2004/02/21
		(interlayer with dielectric) and plug and	US-PGPUB	10:04
		(doping or implantation or implanting)		
_	24	and memory and diode	USPAT;	2004/02/21
/	24	1 ·	US-PGPUB	10:33
		with dielectric) and plug and (doping or	US-PGPUB	10.33
		implantation or implanting) and memory and diode		
8	19		USPAT;	2004/02/21
8	19	with dielectric) and plug and (doping or	US-PGPUB	10:05
		implantation or implanting) and memory	05 10105	
		and diode) not ((isolation with trench)		
		and buried and (interlayer with	1	
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode)		
9	19	(((isolation with trench) and (interlayer	USPAT;	2004/02/21
		with dielectric) and plug and (doping or	US-PGPUB	10:34
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode)) and @ad<20030820		
10	200	, ,	USPAT;	2004/02/21
		(interlayer with dielectric) and (doping	US-PGPUB	11:10
		or implantation or implanting) and memory		
		and bit and word		0004/00/01
11	200		USPAT;	2004/02/21
		(interlayer with dielectric) and (doping	US-PGPUB	10:34
		or implantation or implanting) and memory		
	1	and bit and word) and @ad<20030820	IICDAM.	2004/02/21
12	150		USPAT;	2004/02/21
	1	(interlayer with dielectric) and (doping	US-PGPUB	10:34
		or implantation or implanting) and memory		
1	1	and bit and word) and @ad<20030820) not		1
		((STI and buried and (interlayer with		
		dielectric) and plug and (doping or implantation or implanting) and memory)		
	1	and @ad<20030820)	1	
<u></u>	1	and Gad 200300201	L	

13	132	((((STI or (isolation near3 trench)) and	USPAT;	2004/02/21
	132	(interlayer with dielectric) and (doping	US-PGPUB	10:34
		or implantation or implanting) and memory	4 2 2 3 2 3 2	
		and bit and word) and @ad<20030820) not		
		((STI and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory)		
		and @ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))		
14	62	(((((STI or (isolation near3 trench)) and	1	2004/02/21
		(interlayer with dielectric) and (doping	US-PGPUB	11:08
		or implantation or implanting) and memory		
		and bit and word) and @ad<20030820) not		
		((STI and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory)		
		and @ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)	1	
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
1.5	70	and memory and diode))) and plug ((((STI or (isolation near3 trench)) and	USPAT;	2004/02/21
15	70	(interlayer with dielectric) and (doping	US-PGPUB	10:53
		or implantation or implanting) and memory	05 10102	
		and bit and word) and @ad<20030820) not		
		((STI and buried and (interlayer with		
		dielectric) and plug and (doping or		1
		implantation or implanting) and memory)		
		and @ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
ŀ		implanting) and memory and diode) not		
		((isolation with trench) and buried and		-
		(interlayer with dielectric) and plug and	1	
		(doping or implantation or implanting)		
		and memory and diode))) not (((((STI or		
		(isolation near3 trench)) and (interlayer		
		with dielectric) and (doping or		
		implantation or implanting) and memory		
		and bit and word) and @ad<20030820) not		
		((STI and buried and (interlayer with		
Į		dielectric) and plug and (doping or		
İ		implantation or implanting) and memory)		
		and @ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		1
		and memory and diode))) and plug)		

16	31	(((((STI or (isolation near3 trench))	USPAT;	2004/02/21
		and (interlayer with dielectric) and	US-PGPUB	10:54
		(doping or implantation or implanting)		
		and memory and bit and word) and		
		@ad<20030820) not ((STI and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not		
		(((isolation with trench) and (interlayer		
		with dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory	}	
		and diode))) not (((((STI or (isolation		
		near3 trench)) and (interlayer with		
		dielectric) and (doping or implantation		
		or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
		buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		@ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or		1
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))) and plug)) and		
		buried		

17	39	, , , , , ,	USPAT;	2004/02/21
		and (interlayer with dielectric) and	US-PGPUB	11:08
		(doping or implantation or implanting)		
		and memory and bit and word) and		
		@ad<20030820) not ((STI and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not		
		(((isolation with trench) and (interlayer		
		with dielectric) and plug and (doping or		
1		implantation or implanting) and memory		
		and diode) not ((isolation with trench)		
		and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode))) not (((((STI or (isolation		
		near3 trench)) and (interlayer with		
		dielectric) and (doping or implantation		
		or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
		buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		@ad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric) and plug and (doping or implantation or		
		implanting) and memory and diode) not		
		((isolation with trench) and buried and		İ
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))) and plug)) not		
		(((((((STI or (isolation near3 trench))		1
		and (interlayer with dielectric) and		
		(doping or implantation or implanting)		
		and memory and bit and word) and		
		@ad<20030820) not ((STI and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory) and @ad<20030820)) not		
	:	(((isolation with trench) and (interlayer		
	i	with dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode) not ((isolation with trench)	1	
		and buried and (interlayer with		
		dielectric) and plug and (doping or		
		implantation or implanting) and memory		
		and diode))) not (((((STI or (isolation		
		near3 trench)) and (interlayer with		
		dielectric) and (doping or implantation		
		or implanting) and memory and bit and		
		word) and @ad<20030820) not ((STI and		
	1	buried and (interlayer with dielectric)		
		and plug and (doping or implantation or		
		implanting) and memory) and		
		(dad<20030820)) not (((isolation with		
		trench) and (interlayer with dielectric)		
		and plug and (doping or implantation or implanting) and memory and diode) not		
		((isolation with trench) and buried and		
		(interlayer with dielectric) and plug and		
		(doping or implantation or implanting)		
		and memory and diode))) and plug)) and		
		buried)		
18	0		EPO; JPO;	2004/02/21
1	l	(interlayer with dielectric) and (doping	DERWENT;	11:10
1		or implantation or implanting) and memory	1	
		and bit and word		
	<u> </u>			